



**General Description**

The ZM2301T combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

**Features**

- high cell density Trench technology
- $R_{DS(ON)}$  to minimize conductive loss
- fast switching

**Application**

- Load Switch
- Display Screen Drive

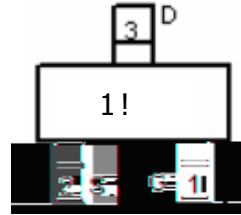
**Product Summary**



- □

- !

- □ (1



"

**Ordering Information:**

	" ! □
	A1H
	REEL TAPE
2	3000

**Absolute Maximum Ratings  $T_c = 25$**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current	$I_{D@TC=25}$	-2.8	A
	$I_{D@TC=75}$	-2.1	A
	$I_{D@TC=100}$	-1.7	A
Pulsed Drain Current	$I_{DM}$	-10	A
Total Power Dissipation	$P_D$	10	W
Total Power Dissipation( $T_A=25$ )	$P_{D@TA=25}$	1.25	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	12.5	C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	100	C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	C

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(TH)}$	V				







Dimensions(SOT23)

Unit mm

